



DMN62D0LFD

N-CHANNEL ENHANCEMENT MODE MOSFET

Product Summary

BV _{DSS}	R _{DS(ON) Max}	I _D T _A = +25°C
60V	2Ω @ $V_{GS} = 4V$	310mA
607	2.5Ω @ $V_{GS} = 2.5V$	295mA

Description and Applications

This new generation MOSFET has been designed to minimize the onstate resistance ($R_{DS(ON)}$) and yet maintain superior switching performance, making it ideal for high efficiency power management applications.

- DC-DC Converters
- Power Management Functions
- Battery Operated Systems and Solid-State Relays
- Drivers: Relays, Solenoids, Lamps, Hammers, Displays, Memories, Transistors, etc.

Features and Benefits

- Low On-Resistance
- Low Input Capacitance
- · Fast Switching Speed
- Low Input/Output Leakage
- ESD Protected
- Totally Lead-Free & Fully RoHS Compliant (Notes 1 & 2)
- Halogen and Antimony Free. "Green" Device (Note 3)
- For automotive applications requiring specific change control (i.e. parts qualified to AEC-Q100/101/200, PPAP capable, and manufactured in IATF 16949 certified facilities), please contact us or your local Diodes representative.

 https://www.diodes.com/quality/product-definitions/

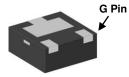
Mechanical Data

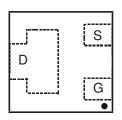
- Case: X1-DFN1212-3
- Case Material: Molded Plastic. UL Flammability Classification Rating 94V-0
- Moisture Sensitivity: Level 1 per J-STD-020
- Terminals: NiPdAu over Copper Leadframe. Solderable per MIL-STD-202, Method 208
- Terminal Connections: See Diagram
- Weight: 0.005 grams (Approximate)

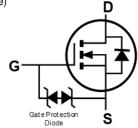




Top View







Bottom View

Pin-Out Top View

Equivalent Circuit

Ordering Information (Note 4)

Part Number	Case	Packaging
DMN62D0LFD-7	X1-DFN1212-3	3,000/Tape & Reel
DMN62D0LFD-13	X1-DFN1212-3	10,000/Tape & Reel

Notes:

- 1. No purposely added lead. Fully EU Directive 2002/95/EC (RoHS), 2011/65/EU (RoHS 2) & 2015/863/EU (RoHS 3) compliant.
- 2. See https://www.diodes.com/quality/lead-free/ for more information about Diodes Incorporated's definitions of Halogen- and Antimony-free, "Green" and Lead-free.
- 3. Halogen- and Antimony-free "Green" products are defined as those which contain <900ppm bromine, <900ppm chlorine (<1500ppm total Br + Cl) and <1000ppm antimony compounds.
- 4. For packaging details, go to our website at https://www.diodes.com/design/support/packaging/diodes-packaging/.

Marking Information



K63 = Product Type Marking Code YM = Date Code Marking Y = Year (ex: H = 2020) M = Month (ex: 9 = September)

Date Code Key

Year	2013		2020	2021	2022	2023	2024	2025	2026	2027	2028	2029
Code	Α		Н	I	J	K	L	М	N	0	Р	R
Month	Jan	Feb	Mar	Apr	May	Jun	Jul	Aug	Sep	Oct	Nov	Dec



Maximum Ratings (@ $T_A = +25^{\circ}C$, unless otherwise specified.)

Characteristic	Symbol	Value	Unit	
Drain-Source Voltage		V_{DSS}	60	V
Gate-Source Voltage		V_{GSS}	±20	V
Continuous Drain Current (Note 5) V _{GS} = 4.0V	$T_A = +25$ °C $T_A = +70$ °C	I _D	310 260	mA
Pulsed Drain Current (Note 6) (10µs Pulse, Duty Cycle = 1%)		I _{DM}	1.0	Α

Thermal Characteristics

Characteristic	Symbol	Max	Unit
Power Dissipation (Note 5)	P_{D}	0.48	W
Thermal Resistance, Junction to Ambient @T _A = +25°C (Note 5)	$R_{\theta JA}$	265	°C/W
Operating and Storage Temperature Range	T _J , T _{STG}	-55 to +150	°C

Electrical Characteristics (@TA = +25°C, unless otherwise specified.)

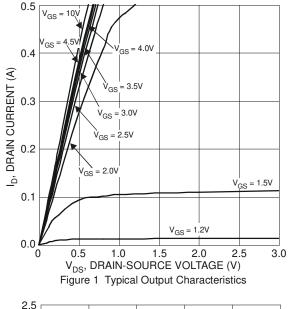
Characteristic	Symbol	Min	Тур	Max	Unit	Test Condition
OFF CHARACTERISTICS (Note 7)			•	•	•	
Drain-Source Breakdown Voltage	BV _{DSS}	60	_	_	V	V _{GS} = 0V, I _D = 250μA
Zero Gate Voltage Drain Current T _J = +25°C	I _{DSS}	_	_	1.0	μΑ	V _{DS} = 60V, V _{GS} = 0V
		_	_	±100	nA	$V_{GS} = \pm 5V$, $V_{DS} = 0V$
Gate-Source Leakage	I _{GSS}	_	_	±500	nA	$V_{GS} = \pm 10V$, $V_{DS} = 0V$
		_	_	±2.0	μA	$V_{GS} = \pm 15V, V_{DS} = 0V$
ON CHARACTERISTICS (Note 7)						
Gate Threshold Voltage	$V_{GS(TH)}$	0.6	_	1.0	V	$V_{DS}=V_{GS},\ I_D=250\mu A$
		1	1.3	2		$V_{GS} = 4V, I_D = 100mA$
Static Drain-Source On-Resistance	В	_	1.4	2.5	Ω	$V_{GS} = 2.5V, I_D = 50mA$
Static Diam-Source On-nesistance	R _{DS(ON)}	1	1.8	3	12	$V_{GS} = 1.8V, I_D = 50mA$
		-	2.4	_		$V_{GS} = 1.5V, I_D = 10mA$
Forward Transfer Admittance	Y _{fs}	_	1.8	_	S	$V_{DS} = 10V, I_D = 200mA$
Diode Forward Voltage	V_{SD}	_	0.8	1.3	V	$V_{GS} = 0V, I_{S} = 115mA$
DYNAMIC CHARACTERISTICS (Note 8)						
Input Capacitance	C _{iss}	-	31	_		
Output Capacitance	Coss	1	4.3	_	pF	$V_{DS} = 25V, V_{GS} = 0V,$ f = 1.0MHz
Reverse Transfer Capacitance	C_{rss}	_	3.0	_		1 – 1.01/11/12
Gate Resistance	R_g	_	99	_	Ω	$V_{DS} = 0V$, $V_{GS} = 0V$, $f = 1MHz$
Total Gate Charge	Qg	_	0.5	_		
Gate-Source Charge	Qgs	_	0.09	_	nC	$V_{GS} = 4.5V, V_{DS} = 10V,$ $I_{D} = 250mA$
Gate-Drain Charge	Q_{gd}	_	0.07	_		ID = 230IIIA
Turn-On Delay Time	t _{D(ON)}	_	2.6	_	ns	
Turn-On Rise Time	t _R		2.1	_	ns	$V_{GS} = 10V, V_{DS} = 30V,$
Turn-Off Delay Time	t _{D(OFF)}	_	18	_	ns	$R_L = 150\Omega, R_G = 25\Omega,$ $I_D = 200\text{mA}$
Turn-Off Fall Time	t _F	_	8.7	_	ns	7 10 - 200 mA

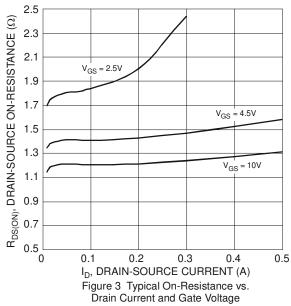
Notes:

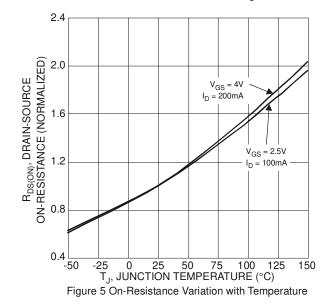
- 5. Device mounted on FR-4 PCB with minimum recommended pad layout, single sided.6. Repetitive rating, pulse width limited by junction temperature.7. Short duration pulse test used to minimize self-heating effect.

- 8. Guaranteed by design. Not subject to production testing.

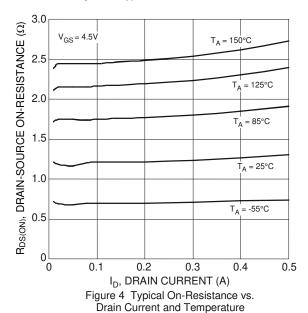








0.5 $V_{DS} = 5.0V$ 0.4 ID, DRAIN CURRENT (A) 0.3 0.2 0.1 -55°C 0 0.5 1.0 1.5 2.0 2.5 V_{GS}, GATE-SOURCE VOLTAGE (V) Figure 2 Typical Transfer Characteristics



3.0 $R_{DS(ON)}$, DRAIN-SOURCE ON-RESISTANCE (Ω) 2.5 $V_{GS} = 2.5V$ I_D = 100mA 2.0 $V_{GS} = 4V$ I_D = 200mA 1.5 1.0 0.5 0 <u></u> -25 25 50 75 100 125 T_{.I}, JUNCTION TEMPERATURE (°C)

Figure 6 On-Resistance Variation with Temperature



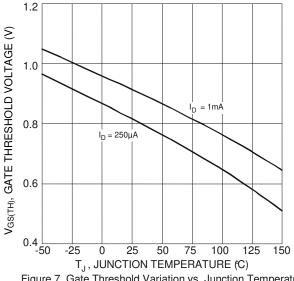
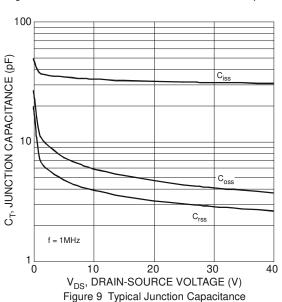
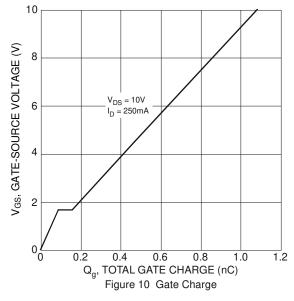


Figure 7 Gate Threshold Variation vs. Junction Temperature



0.5 0.4 Is, SOURCE CURRENT (A) 0.3 $T_A = 25^{\circ}C$ 0.2 0.1 0 _ 0.6 0.3 0.9 1.2 1.5 V_{SD}, SOURCE-DRAIN VOLTAGE (V) Figure 8 Diode Forward Voltage vs. Current



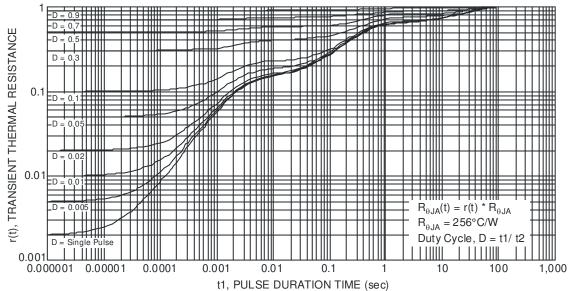


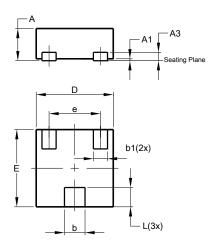
Figure 11 Transient Thermal Resistance



Package Outline Dimensions

Please see http://www.diodes.com/package-outlines.html for the latest version.

X1-DFN1212-3

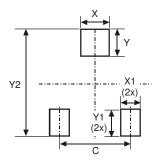


X1-DFN1212-3						
Dim	Min	Max	Тур			
Α	0.47	0.53	0.50			
A1	0	0.05	0.02			
A3	-	1	0.13			
b	0.27	0.37	0.32			
b1	0.17	0.27	0.22			
D	1.15	1.25	1.20			
Е	1.15	1.25	1.20			
е	-	-	0.80			
Ĺ	0.25	0.35	0.30			
All D	imens	ions i	n mm			

Suggested Pad Layout

Please see http://www.diodes.com/package-outlines.html for the latest version.

X1-DFN1212-3



Dimensions	Value (in mm)
С	0.80
Х	0.42
X1	0.32
Υ	0.50
Y1	0.50
Y2	1.50



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